

INCHANGE SEMICONDUCTOR

isc Silicon NPN Power Transistor

BDX75

DESCRIPTION

- · Collector-Emitter Breakdown Voltage-
- : V_{(BR)CEO}= 40V (Min)
- High Current Capability
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

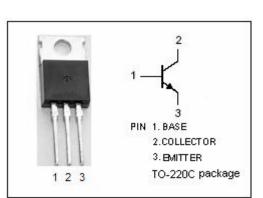
APPLICATIONS

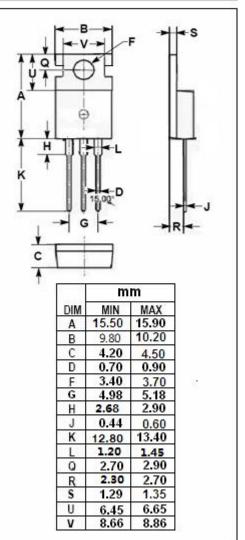
• Designed for use in general-purpose amplifier and switching applications.

| ABSOLUTE MAXIMUM RATINGS(Ta=25°C) | | | | | | | |
|-----------------------------------|---|---------|------|--|--|--|--|
| SYMBOL | PARAMETER | VALUE | UNIT | | | | |
| V _{CBO} | Collector-Base Voltage | 45 | V | | | | |
| V _{CEO} | Collector-Emitter Voltage | 40 | V | | | | |
| V _{EBO} | Emitter-Base Voltage | 6 | V | | | | |
| Ι _C | Collector Current-Continuous | 16 | А | | | | |
| Pc | Collector Power Dissipation @ $T_c=25^{\circ}C$ | on 75 | | | | | |
| TJ | Junction Temperature | 150 | °C | | | | |
| T _{stg} | Storage Temperature Range | -65~150 | °C | | | | |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | МАХ | UNIT |
|---------------------|---|------|------|
| R _{th j-c} | Thermal Resistance, Junction to Case | 1.67 | °C/W |
| R _{th j-a} | Thermal Resistance, Junction to Ambient | 70 | °C/W |







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ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}C$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | МАХ | UNIT |
|----------------------|--------------------------------------|---|-----|-----------|------|
| Vceo(sus) | Collector-Emitter Sustaining Voltage | I _C = 50mA; I _B = 0 | 40 | | V |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = 16A; I _B = 3.2A | | 2.5 | V |
| V _{BE(on)} | Base-Emitter On Voltage | I _C = 8A ; V _{CE} = 4V | | 1.7 | V |
| ICEX | Collector Cutoff Current | V _{CE} = 45V; V _{BE} = -1.5V V _{CE} = 45V; V _{BE} = -1.5V;T _C =150℃ | | 2.0 10 | mA |
| I _{CEO} | Collector Cutoff Current | V _{CE} = 40V; I _B = 0 | | 2.0 | mA |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 8V; I _C = 0 | | 1.0 | mA |
| h _{FE-1} | DC Current Gain | I _C = 8A ; V _{CE} = 4V | 15 | 60 | |
| h _{FE-2} | DC Current Gain | I _C = 16A ; V _{CE} = 4V | 5 | | |
| f⊤ | Current-Gain—Bandwidth Product | I _C = 1A ; V _{CE} = 4V, f _{test} = 0.1MHz | 3 | | MHz |

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